

PROCESS CP275

Power Transistor

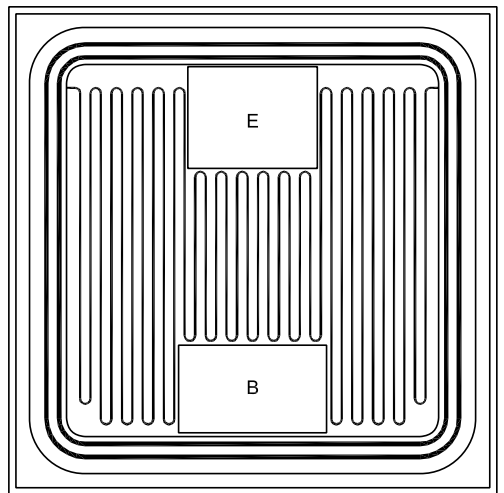
[查询"CP275"供应商](#) 4.0 Amp NPN Silicon Power Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Die Size	105 x 105 MILS
Die Thickness	8.5 MILS
Base Bonding Pad Area	32 x 19 MILS
Emitter Bonding Pad Area	28 x 22 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Ti/Ni/Ag - (300Å, 1,000Å, 10,000Å)

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

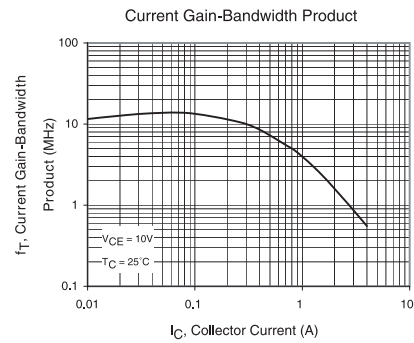
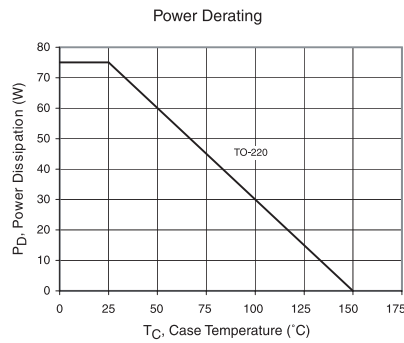
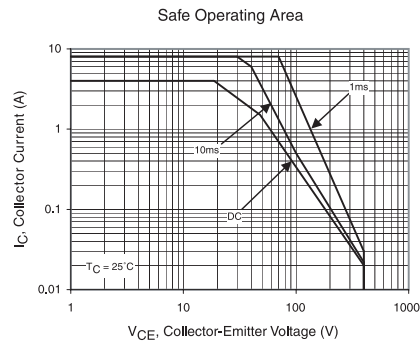
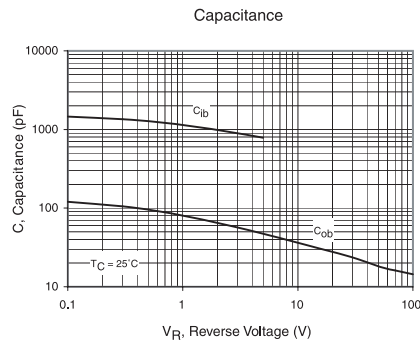
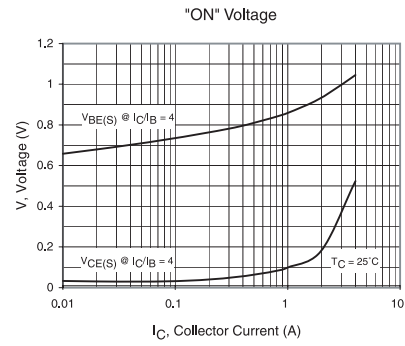
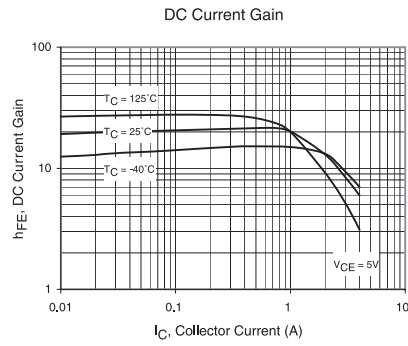
980

PRINCIPAL DEVICE TYPES

MJE13005

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R1 (28-March 2005)



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